TOSHIBA CMOS Didital Integrated Circuit Silicon Monolithic

# TC7MET139AFK

Dual 2-to-4 Line Decoder

The TC7MET139AFK is an advanced high speed CMOS 2 to 4 line decoder/demultiplexer fabricated with silicon gate  ${\rm C^2MOS}$  technology.

It achieves the high speed operation similar to equivalent bipolar schottky TTL while maintaining the CMOS low power dissipation.

The active low enable input can be used for gating or it can be used as a data input for demultiplexing applications.

When the enable input is held High, all four outputs are fixed at a high logic level independent of the other inputs.

The input voltage are compatible with TTL output voltage.

This device may be used as a level converter for interfacing 3.3 V to 5 V system.



Weight: 0.02 g (typ.)

Input protection and output circuit ensure that 0 to 5.5 V can be applied to the input and output (\*) pins without regard to the supply voltage. These structure prevents device destruction due to mismatched supply and input/output voltages such as battery back up, hot board insertion, etc.

\*: V<sub>CC</sub> = 0 V

#### **Features**

- High speed:  $t_{pd} = 5.0 \text{ ns (typ.) (VCC} = 5 \text{ V)}$
- Low power dissipation: ICC = 4 μA (max) (Ta = 25°C)
- Compatible with TTL outputs: VIL = 0.8 V (max)VIH = 2.0 V (min)
- Power down protection is provided on all inputs and outputs.
- Balanced propagation delays:  $t_pLH \approx t_pHL$
- Low noise: VOLP = 0.8 V (max)
- Pin and function compatible with the 74 series (74AC/HC/F/ALS/LS etc.) 139 type.

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damage to property.

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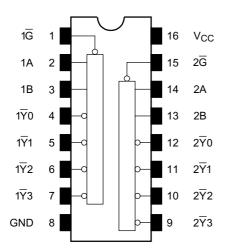
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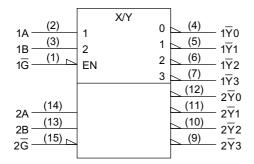
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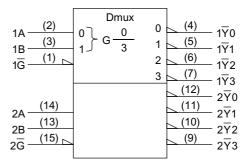
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# Pin Assignment (top view)



# **IEC Logic Symbol**





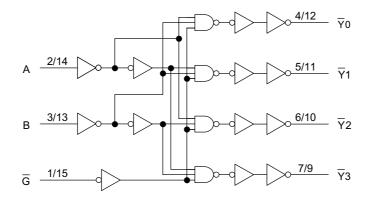
### **Truth Table**

Inputs				Out	puts							
Enable	Select		<u></u>	<u>7</u> 1	<u>7</u> 2	_ Y3	Selected Output					
G	В	Α	10	11	12	13						
Н	Х	Х	Н	Н	Н	Н	None					
L	L	L	L	Н	Н	Н	₹0					
L	L	Н	Н	L	Н	Н	<del>Y</del> 1					
L	Н	L	Н	Н	Ĺ	Н	Ÿ2					
L	Н	Н	Н	Н	Н	L	Ÿ3					

X: Don't care



# **System Diagram**



# **Maximum Ratings**

Characteristics	Symbol	Rating	Unit	
Supply voltage range	V <sub>CC</sub>	-0.5~7.0	V	
DC input voltage	V <sub>IN</sub>	-0.5~7.0	V	
DC output voltage	V	-0.5~7.0 (Note1)	V	
DC output voltage	Vout	-0.5~V <sub>CC</sub> + 0.5 (Note2)	V	
Input diode current	l <sub>IK</sub>	-20	mA	
Output diode current	lok	±20 (Note3)	mA	
DC output current	lout	±25	mA	
DC V <sub>CC</sub> /ground current	Icc	±50	mA	
Power dissipation	PD	180	mW	
Storage temperature	T <sub>stg</sub>	-65~150	°C	

Note1:  $V_{CC} = 0 V$ 

Note2: High or low state. IOUT absolute maximum rating must be observed.

Note3:  $V_{OUT} < GND, V_{OUT} > V_{CC}$ 

# **Recommended Operating Conditions**

Characteristics	Symbol	Rating	Unit
Supply voltage	V <sub>CC</sub>	4.5~5.5	V
Input voltage	V <sub>IN</sub>	0~5.5	٧
Output voltage	V	0~5.5 (Note4)	V
Output voltage	V <sub>OUT</sub>	0~V <sub>CC</sub> (Note5)	V
Operating temperature	T <sub>opr</sub>	-40~85	°C
Input rise and fall time	dt/dv	0~20	ns/V

Note4:  $V_{CC} = 0 V$ 

Note5: High or low state.



### **Electrical Characteristics**

### **DC Characteristics**

Characteristics		Symbol	Test Condition			Ta = 25°C			Ta = -40~85°C		Unit
		Symbol			V <sub>CC</sub> (V)	Min	Тур.	Max	Min	Max	Unit
Input voltage	High level	V <sub>IH</sub>	_		4.5~5.5	2.0	_	_	2.0	_	V
	Low level	V <sub>IL</sub>	_		4.5~5.5	_	_	0.8	_	0.8	
Output voltage	High level	V <sub>OH</sub>	V <sub>IN</sub> = V <sub>IH</sub> or V <sub>IL</sub>	$I_{OH} = -50 \mu A$	4.5	4.4	4.5	_	4.4	_	V
				$I_{OH} = -8 \text{ mA}$	4.5	3.94	_	_	3.80	_	
	Low level	V <sub>OL</sub>	V <sub>IN</sub> = V <sub>IH</sub> or V <sub>IL</sub>	$I_{OL} = 50  \mu A$	4.5	_	0	0.1	_	0.1	
				I <sub>OL</sub> = 8 mA	4.5	_	_	0.36	_	0.44	
Input leakage current		I <sub>IN</sub>	V <sub>IN</sub> = 5.5 V or GND		0~5.5	_	_	±0.1	_	±1.0	μΑ
Quiescent supply current		I <sub>CC</sub>	V <sub>IN</sub> = V <sub>CC</sub> or GND		5.5	_	_	4.0	_	40.0	μΑ
		I <sub>CCT</sub>	Per input: V <sub>IN</sub> = 3.4 V Other input: V <sub>CC</sub> or GND		5.5	_	_	1.35	_	1.50	mA
Output leakage current		I <sub>OPD</sub>	V <sub>OUT</sub> = 5.5 V		0		_	0.5	_	5.0	μА

### AC Characteristics (Input: $t_r = t_f = 3 \text{ ns}$ )

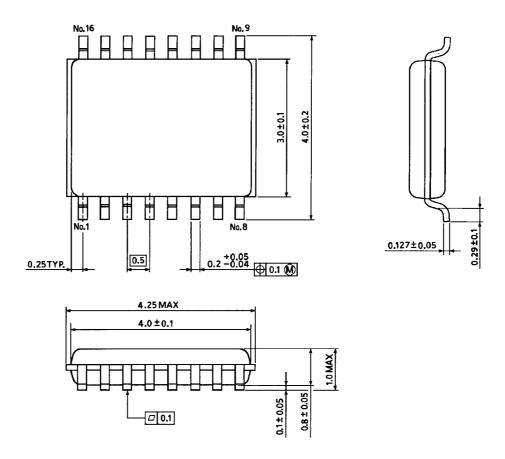
Characteristics	Symbol	Test Condition			Ta = 25°C			Ta = -40~85°C		Unit
Characteristics	Symbol	rest Condition	V <sub>CC</sub> (V)	C <sub>L</sub> (pF)	Min	Тур.	Max	Min	Max	Offic
Propagation delay time	t <sub>pLH</sub>	_	5.0 ± 0.5	15	_	5.0	7.2	1.0	8.5	- ns
$(A, B-\overline{Y})$	t <sub>pHL</sub>			50	_	6.5	9.2	1.0	10.5	
Propagation delay time	t <sub>pLH</sub>		5.0 ± 0.5	15	_	5.0	7.2	1.0	8.5	ns
(G-Y)	tpHL	_		50	_	6.5	9.2	1.0	10.5	113
Input capacitance	ance C <sub>IN</sub>		_		_	4	10	_	10	pF
Power dissipation capacitance	C <sub>PD</sub>			(Note6)		32	_	_	_	pF

Note6: C<sub>PD</sub> is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation:

 $I_{CC (opr)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}/2 \text{ (per decoder)}$ 

# **Package Dimensions**



Weight: 0.02 g (typ.)